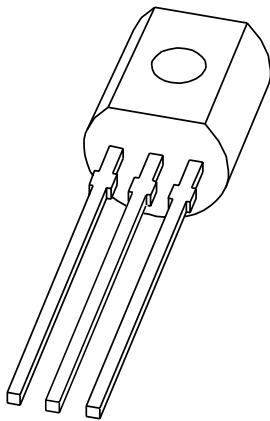


DATA SHEET



BF324

PNP medium frequency transistor

Product specification
Supersedes data of 1997 Jul 07

2004 Nov 05

PNP medium frequency transistor

BF324

FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 30 V).

APPLICATIONS

- RF stages in FM front-ends in common base configuration.

DESCRIPTION

PNP medium frequency transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector

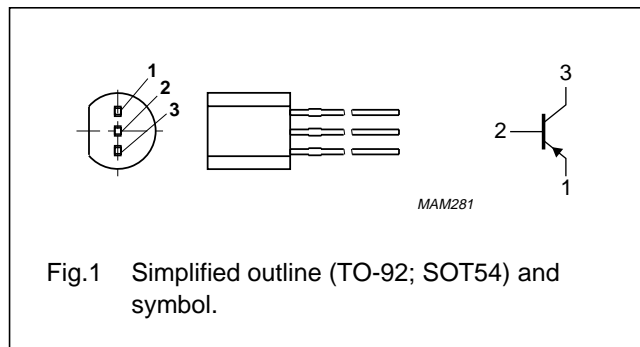


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	–30	V
V_{CEO}	collector-emitter voltage	open base	–	–	–30	V
I_{CM}	peak collector current		–	–	–25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	–	300	mW
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}; I_C = -4\text{ mA}$	25	–	–	
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -4\text{ mA}; f = 100\text{ MHz}$	–	450	–	MHz

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF324	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

PNP medium frequency transistor

BF324

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–30	V
V_{CEO}	collector-emitter voltage	open base	–	–30	V
V_{EBO}	emitter-base voltage	open collector	–	–4	V
I_C	collector current (DC)		–	–25	mA
I_{CM}	peak collector current		–	–25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	420	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}$; $I_E = 0\text{ A}$	–	–	–50	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -4\text{ V}$; $I_C = 0\text{ A}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -10\text{ V}$ $I_C = -1\text{ mA}$ $I_C = -4\text{ mA}$	– 25	45 –	– –	
V_{BE}	base-emitter voltage	$V_{CE} = -10\text{ V}$; $I_C = -4\text{ mA}$	–	760	–	mV
C_{rb}	feedback capacitance	$V_{CE} = -10\text{ V}$; $I_C = 0\text{ A}$; $f = 1\text{ MHz}$	–	–	0.3	pF
f_T	transition frequency	$V_{CE} = -10\text{ V}$; $f = 100\text{ MHz}$ $I_C = -1\text{ mA}$ $I_C = -4\text{ mA}$ $I_C = -8\text{ mA}$	– 400 –	350 450 440	– – –	MHz MHz MHz

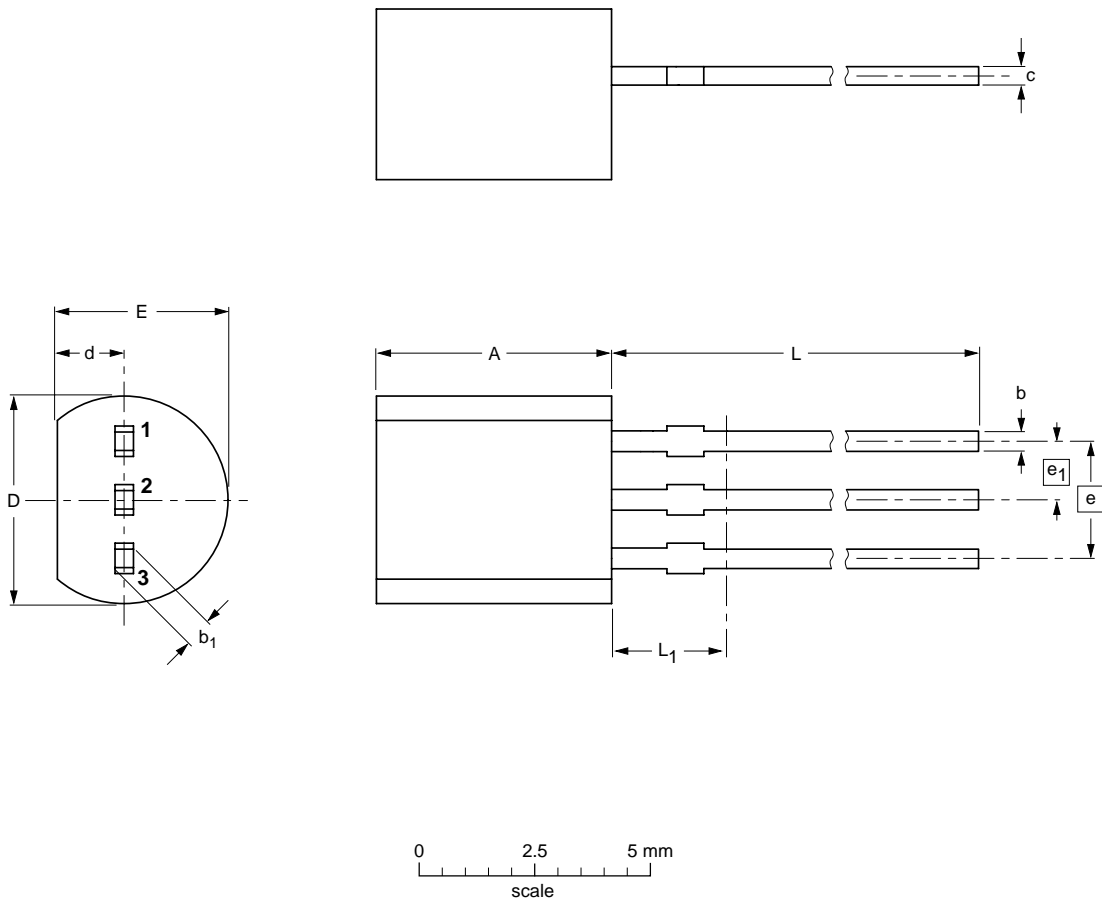
PNP medium frequency transistor

BF324

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		97-02-28 04-06-28

PNP medium frequency transistor

BF324

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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SCA76

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